NDPL070N10B

Advance Information

Power MOSFET 100V, 10.8mΩ, 70A, N-Channel

ON Semiconductor®

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Features

- Low On-Resistance
- Low Gate Charge
- High Speed Switching
- 100% Avalanche Tested
- Pb-Free and RoHS Compliance

Applications

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	100	٧
Gate to Source Voltage	V _{GSS}	±20	V
Drain Current (DC)	ID	70	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	280	Α
Power Dissipation Tc=25°C	PD	2.1 72	W
Junction Temperature	Tj	175	°C
Storage Temperature	Tstg	–55 to +175	°C
Source Current (Body Diode)	Is	70	Α
Avalanche Energy (Single Pulse) *1	EAS	82	mJ
Lead Temperature for Soldering Purposes, 3mm from Case for 10 Seconds	TL	260	°C

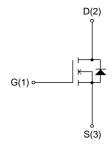
Thermal Resistance Ratings

Parameter	Symbol	Value	Unit	
Junction to Case Steady State	$R_{ heta JC}$	2.08	°C/W	
Junction to Ambient *2	R ₀ JA	71.4] 0/44	

Note : *1 VDD=48V, L=100 μ H, IAV=30A (Fig.1)

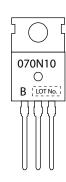
VDSS	R _{DS} (on) Max	ID Max
100V	10.8 mΩ@15V	704
	12.8 mΩ@10V	70A

Electrical Connection N-Channel



Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*2} Insertion mounted

NDPL070N10B

Electrical Characteristics at Ta = 25°C

Parameter	Cumbal	Conditions	Value			11:4
Parameter	Symbol		min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =10mA, V _{GS} =0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0V			10	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	2		4	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =35A	V _{DS} =10V, I _D =35A			S
	R _{DS} (on)1	I _D =35A, V _{GS} =15V		9.0	10.8	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =35A, V _{GS} =10V		9.8	12.8	mΩ
Input Capacitance	Ciss			2,010		pF
Output Capacitance	Coss	V _{DS} =50V, f=1MHz		840		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t _d (on)			30		ns
Rise Time	t _r	050		180		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		55		ns
Fall Time	tf			40		ns
Total Gate Charge	Qg			26		nC
Gate to Source Charge	Qgs	V _{DS} =48V, V _{GS} =10V, I _D =70A		9		nC
Gate to Drain "Miller" Charge	Qgd			8		nC
Forward Diode Voltage	V _{SD}	I _S =70A, V _{GS} =0V		1.1	1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		95		ns
Reverse Recovery Charge	Q _{rr}	I _S =70A, V _{GS} =0V, di/dt=100A/μs		240		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Fig.1 Unclamped Inductive Switching Test Circuit

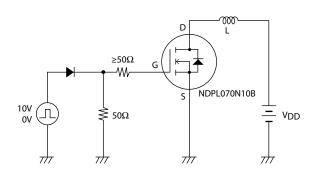


Fig.3 Reverse Recovery Time Test Circuit

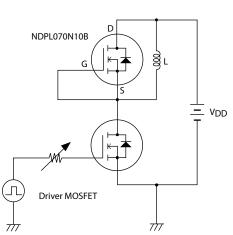
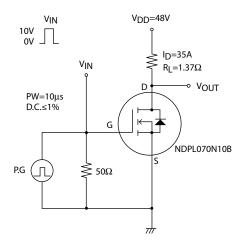
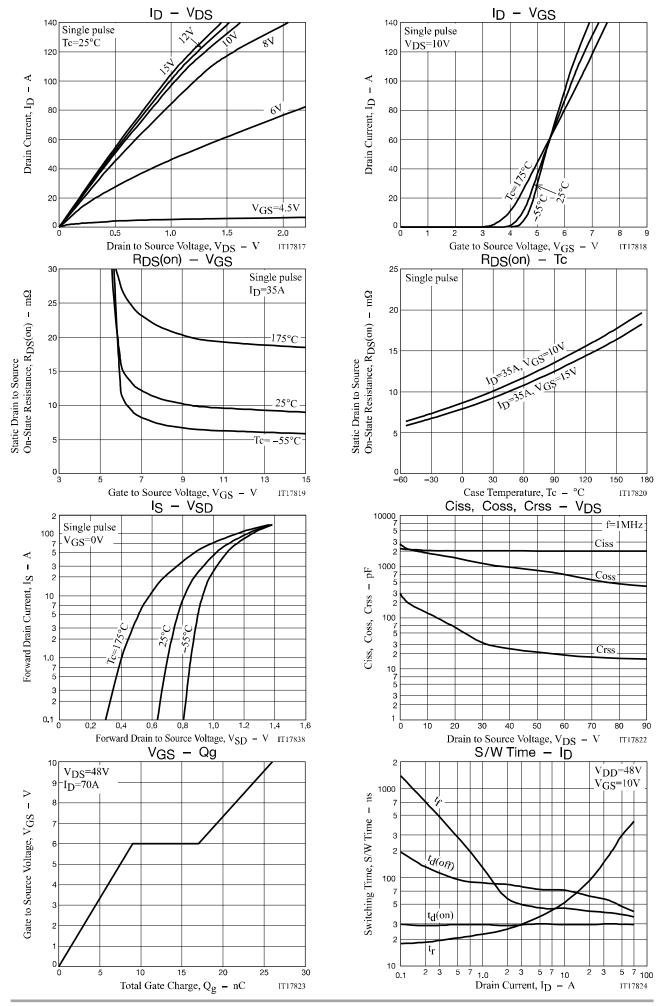
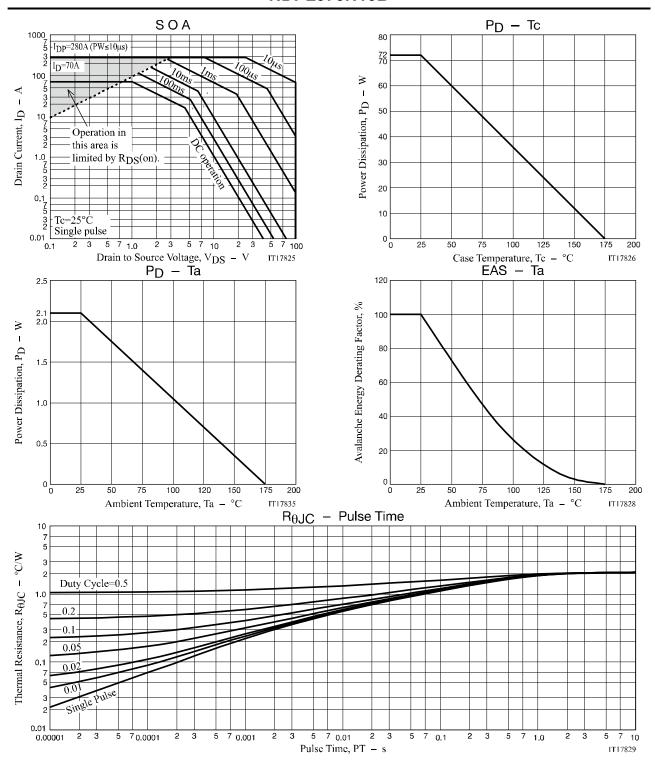


Fig.2 Switching Time Test Circuit





NDPL070N10B



Package Dimensions

NDPL070N10BG

TO-220, 3-Lead/TO-220-3L

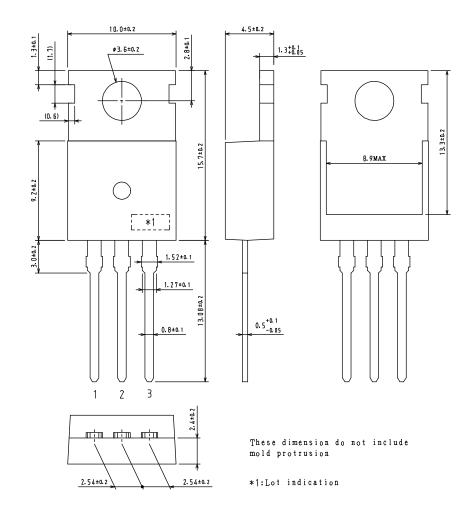
CASE 221AU ISSUE O

unit: mm

1:Gate

2:Drain

3:Source



ORDERING INFORMATION

Device	Package	Shipping	note
NDPL070N10BG	TO-220-3L SC-46,TO-220AB	50 pcs. / tube	Pb-Free

Note on usage: Since the NDPL070N10B is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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